

**30V P-CHANNEL ENHANCEMENT MODE MOSFET
 POWERDI®**
Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ max}$	$I_D \text{ max}$ $T_A = +25^\circ\text{C}$
-30V	20mΩ @ $V_{GS} = -10\text{V}$	- 8.7 A
	29mΩ @ $V_{GS} = -5\text{V}$	-7.2 A

Features and Benefits

- Low $R_{DS(ON)}$ – ensures on state losses are minimized.
- Small form factor thermally efficient package enables higher density end products.
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product.
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Description and Applications

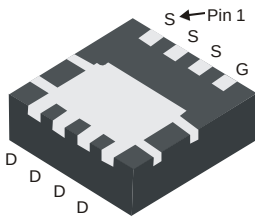
This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

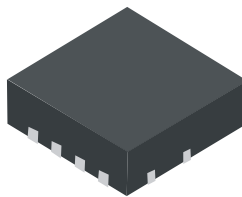
Mechanical Data

- Case: POWERDI3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
Terminals: Finish – Matte Tin Annealed over Copper Leadframe.
Solderable per MIL-STD-202, Method 208@3
- Weight: 0.03 grams (Approximate)

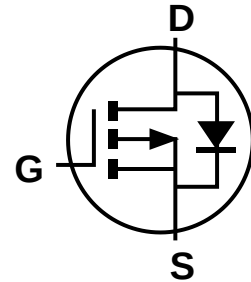
POWERDI®3333-8



Bottom View



Top View



Equivalent Circuit

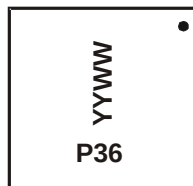
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3036SFG-7	POWERDI3333-8	2,000/Tape & Reel
DMP3036SFG-13	POWERDI3333-8	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information

POWERDI®3333-8



P36 = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Digit of Year (ex: 14 = 2014)
 WW = Week Code (01 ~ 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	T _A = +25°C T _A = +70°C	I _D	-8.7 -7.0	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	-12.7 -10.1	A
Continuous Drain Current (Note 6) V _{GS} = -5V	Steady State	T _A = +25°C T _A = +70°C	I _D	-7.2 -5.8	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	-10.5 -8.4	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I _{DM}	-80	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	-3.6	A
Avalanche Current (Note 7) L=0.3 mH			I _{AS}	-17.5	A
Avalanche Energy (Note 7) L=0.3 mH			E _{AS}	64	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P _D	0.95	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	137	°C/W
	t < 10s		65	°C/W
Total Power Dissipation (Note 6)		P _D	2.3	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	55	°C/W
	t < 10s		26	°C/W
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	6.14	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	-	-	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	-	-	-1.0	μA	V _{DS} = -30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	V _{GS} = ±25V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	-1.0	-2.0	-2.5	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	-	13	20	mΩ	V _{GS} = -10V, I _D = -8A
		-	18.4	29		V _{GS} = -5V, I _D = -5A
Diode Forward Voltage	V _{SD}	-	-0.74	-1.0	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	-	1931	-	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	226	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	168	-	pF	
Gate Resistance	R _g	-	10.9	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge V _{GS} = -5V	Q _g	-	8.8	-	nC	V _{DS} = -15V, V _{GS} = -10V, I _D = -10A
Total Gate Charge V _{GS} = -10V	Q _g	-	16.5	-	nC	
Gate-Source Charge	Q _{gs}	-	2.6	-	nC	
Gate-Drain Charge	Q _{gd}	-	3.6	-	nC	
Turn-On Delay Time	t _{D(on)}	-	8.2	-	ns	V _{GEN} = -10V, V _{DD} = -15V, R _{GEN} = 3Ω, I _D = -10A
Turn-On Rise Time	t _r	-	14	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	65	-	ns	
Turn-Off Fall Time	t _f	-	31.6	-	ns	

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 7. UIS in production with L = 0.1mH, starting T_A = +25°C.
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to product testing.

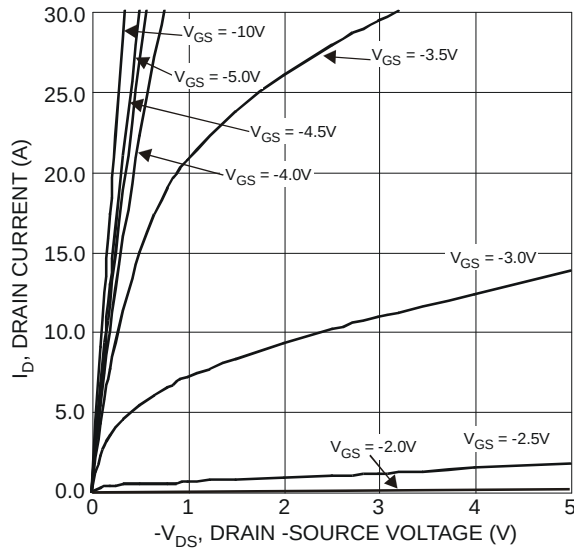


Figure 1 Typical Output Characteristics

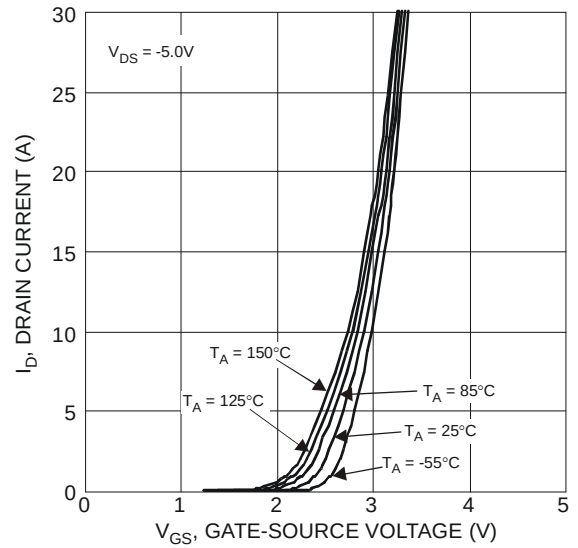


Figure 2 Typical Transfer Characteristics

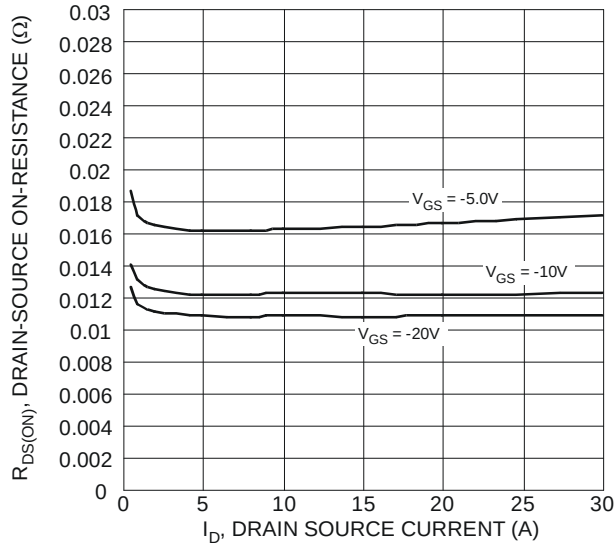


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

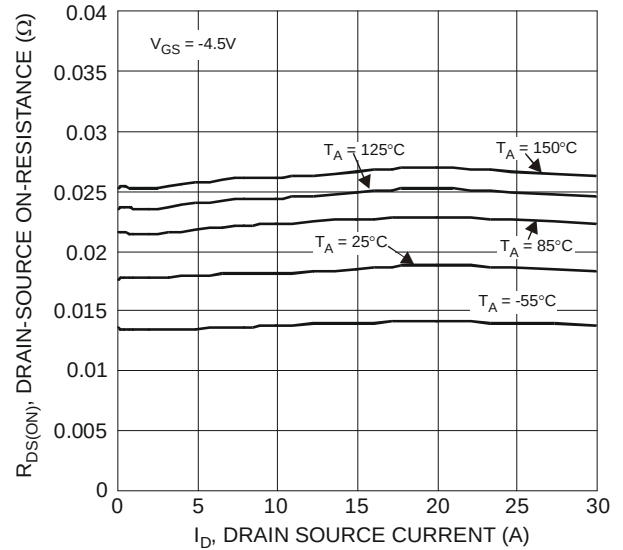


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

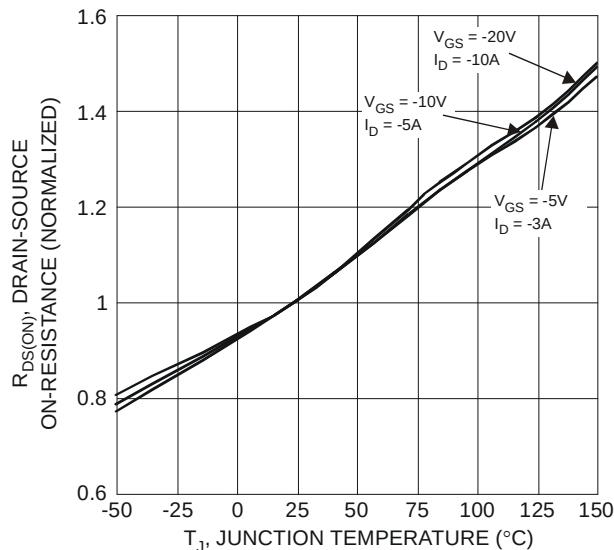


Figure 5 On-Resistance Variation with Temperature

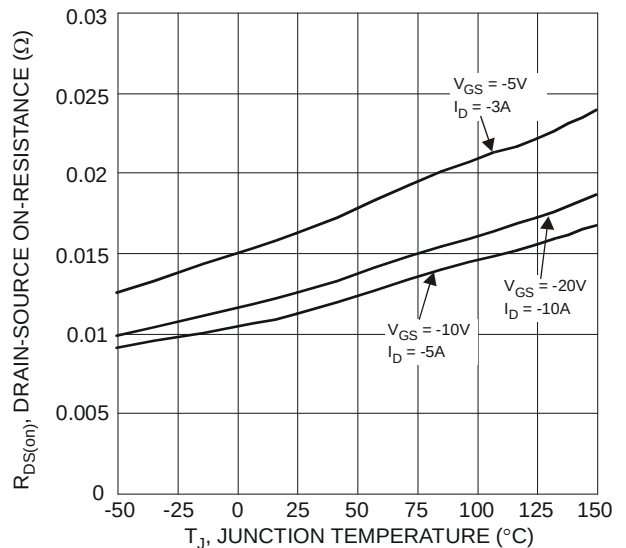


Figure 6 On-Resistance Variation with Temperature

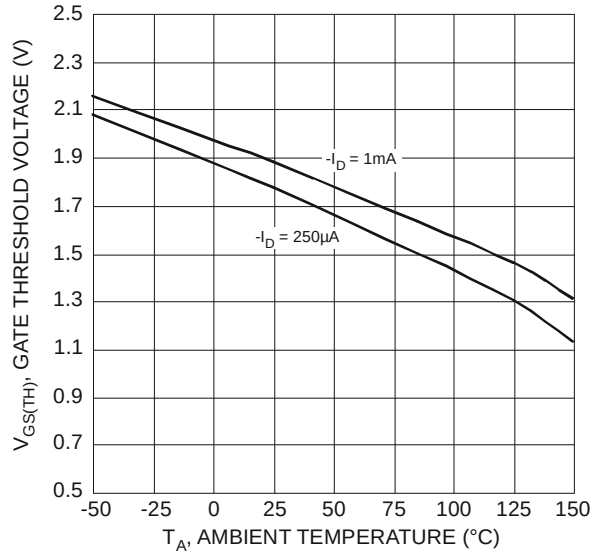


Figure 7 Gate Threshold Variation vs. Ambient Temperature

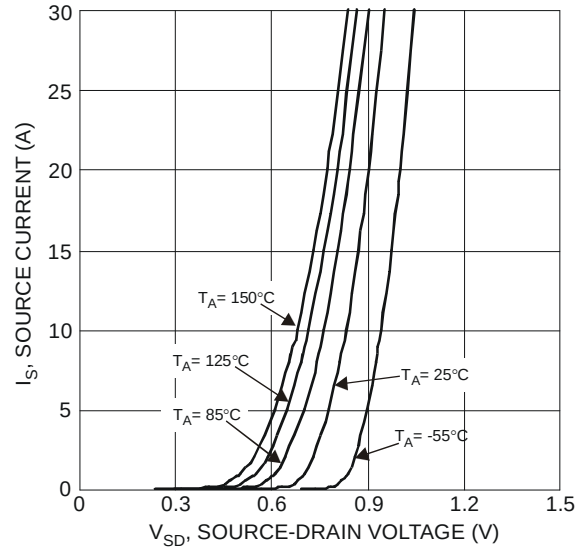


Figure 8 Diode Forward Voltage vs. Current

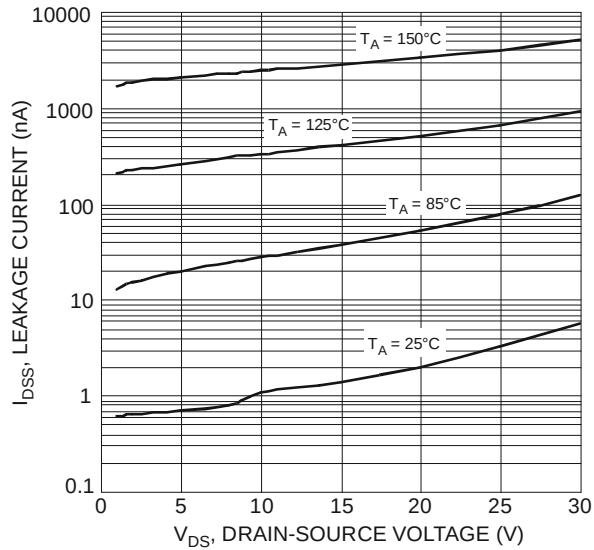


Figure 9 Typical Drain-Source Leakage Current vs. Voltage

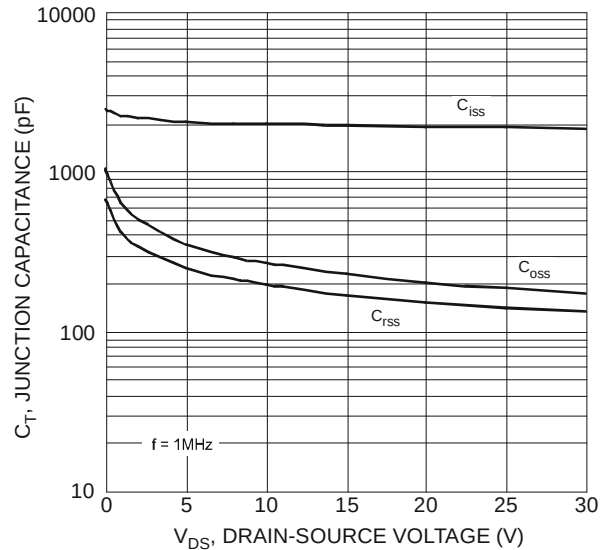


Figure 10 Typical Junction Capacitance

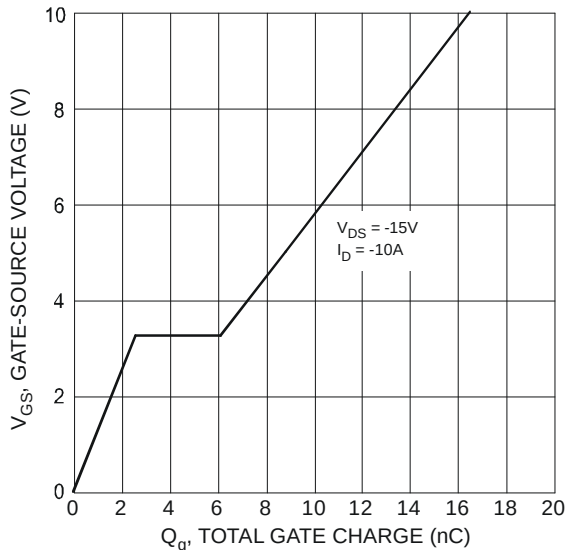


Figure 11 Gate-Charge Characteristics

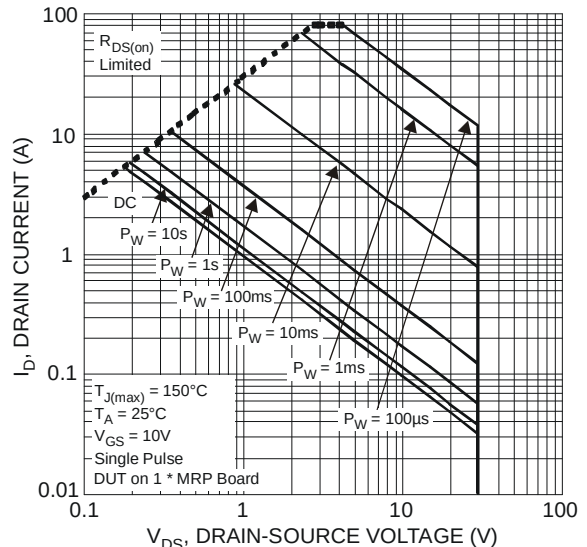
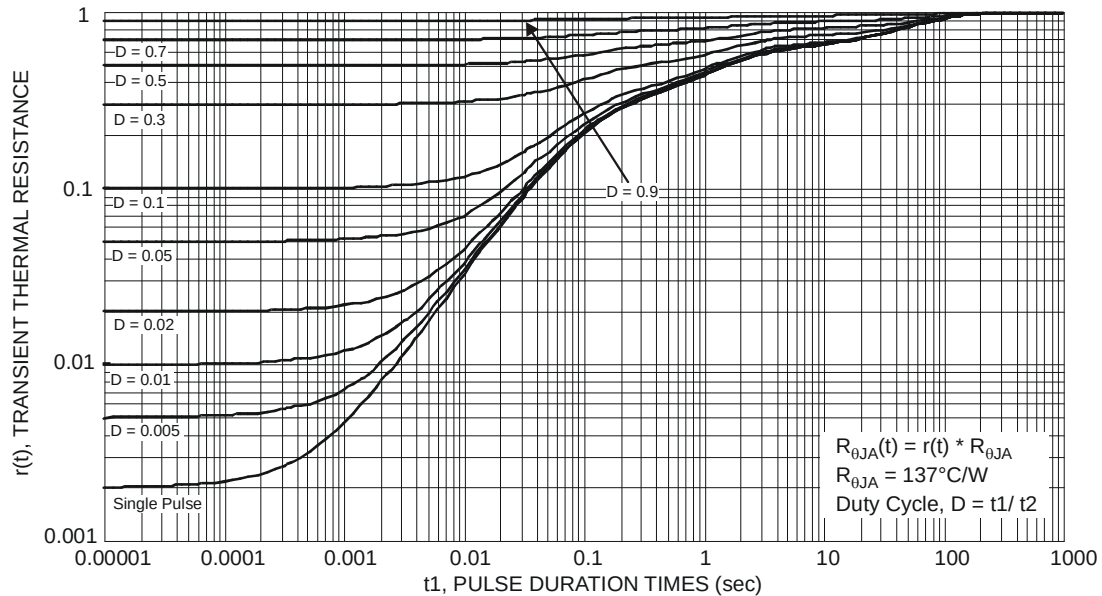
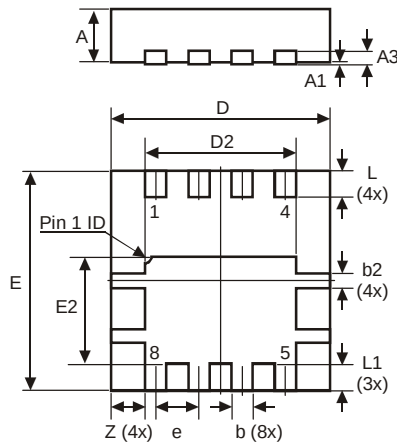


Figure 12 SOA, Safe Operation Area



Package Outline Dimensions

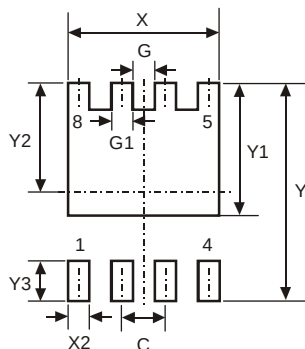
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



POWERDI3333-8			
Dim	Min	Max	Typ
D	3.25	3.35	3.30
E	3.25	3.35	3.30
D2	2.22	2.32	2.27
E2	1.56	1.66	1.61
A	0.75	0.85	0.80
A1	0	0.05	0.02
A3	—	—	0.203
b	0.27	0.37	0.32
b2	—	—	0.20
L	0.35	0.45	0.40
L1	—	—	0.39
e	—	—	0.65
Z	—	—	0.515
All Dimensions in mm			

Suggested Pad Layout

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.650
G	0.230
G1	0.420
Y	3.700
Y1	2.250
Y2	1.850
Y3	0.700
X	2.370
X2	0.420

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